

BUK9M12-60EX Datasheet

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DiGi Electronics Part Number

Manufacturer Product Number

Description

Manufacturer

Detailed Description

BUK9M12-60EX-DG

Nexperia USA Inc.

BUK9M12-60EX

MOSFET N-CH 60V 54A LFPAK33

N-Channel 60 V 54A (Tc) 79W (Tc) Surface Mount LF PAK33

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Manufacturer Product Number:	Manufacturer:
BUK9M12-60EX	Nexperia USA Inc.
Series:	Product Status:
TrenchMOS™	Active
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (ld) @ 25°C:
60 V	54A (Tc)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ ld, Vgs:
5V	11mOhm @ 15A, 10V
Vgs(th) (Max) @ ld:	Vgs (Max):
2.1V @ 1mA	±10V
Input Capacitance (Ciss) (Max) @ Vds:	FET Feature:
2769 pF @ 25 V	
Power Dissipation (Max):	Operating Temperature:
79W (Tc)	-55°C ~ 175°C (TJ)
Grade:	Qualification:
Automotive	AEC-Q101
Mounting Type:	Supplier Device Package:
Surface Mount	LFPAK33
Package / Case:	Base Product Number:
SOT-1210, 8-LFPAK33 (5-Lead)	BUK9M12

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.29.0095	



BUK9M12-60E

N-channel 60 V, 12 mΩ logic level MOSFET in LFPAK3319 September 2016Product data sheet

1. General description

Logic level N-channel MOSFET in an LFPAK33 (Power33) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with V_{GS(th)} rating of greater than 0.5 V at 175 °C

3. Applications

- 12 V automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Qui	ck reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	-	60	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>	-	-	54	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	-	79	W
Static charact	eristics					
R _{DSon}	drain-source on-state resistance	V _{GS} = 5 V; I _D = 15 A; T _j = 25 °C; <u>Fig. 11</u>	-	10	12	mΩ
Dynamic char	acteristics					
Q _{GD}	gate-drain charge	$I_D = 15 \text{ A}; V_{DS} = 48 \text{ V}; V_{GS} = 5 \text{ V};$ $T_j = 25 \text{ °C}; \text{ Fig. 13}; \text{ Fig. 14}$	-	7.9	-	nC

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N-channel 60 V, 12 m Ω logic level MOSFET in LFPAK33

5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	Source		D
2	S	Source		
3	S	Source	\bigcirc	G-UF4
4	G	Gate		mbb076 S
mb	D	Mounting base; connected to drain	LFPAK33 (SOT1210)	

6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
BUK9M12-60E	LFPAK33	Plastic single ended surface mounted package (LFPAK33); 8 leads	SOT1210			

7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK9M12-60E	91260E

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	60	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ		-	60	V
V _{GS}	gate-source voltage	DC; T _j ≤ 175 °C		-10	10	V
		Pulsed; T _j ≤ 175 °C	[1][2]	-15	15	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	79	W
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>		-	54	А
		V _{GS} = 5 V; T _{mb} = 100 °C; <u>Fig. 2</u>		-	38	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$; Fig. 3		-	216	А

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N-channel 60 V, 12 m Ω logic level MOSFET in LFPAK33

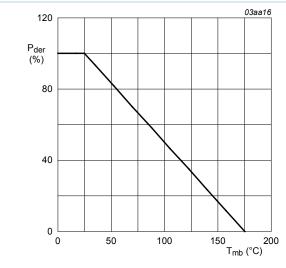
Symbol	Parameter	Conditions		Min	Max	Unit
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-dra	in diode					
I _S	source current	T _{mb} = 25 °C		-	54	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$		-	216	А
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 54 A; V _{sup} ≤ 60 V; R _{GS} = 50 Ω; V _{GS} = 5 V; T _{j(init)} = 25 °C; unclamped; Fig. 4	[3][4]	-	50.5	mJ

[1] Accumulated pulse duration up to 50 hours delivers zero defect ppm.

[2] Significantly longer life times are achieved by lowering T_i and or V_{GS}

[3] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

[4] Refer to application note AN10273 for further information.





$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

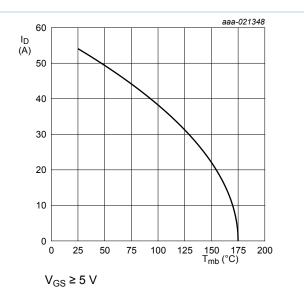


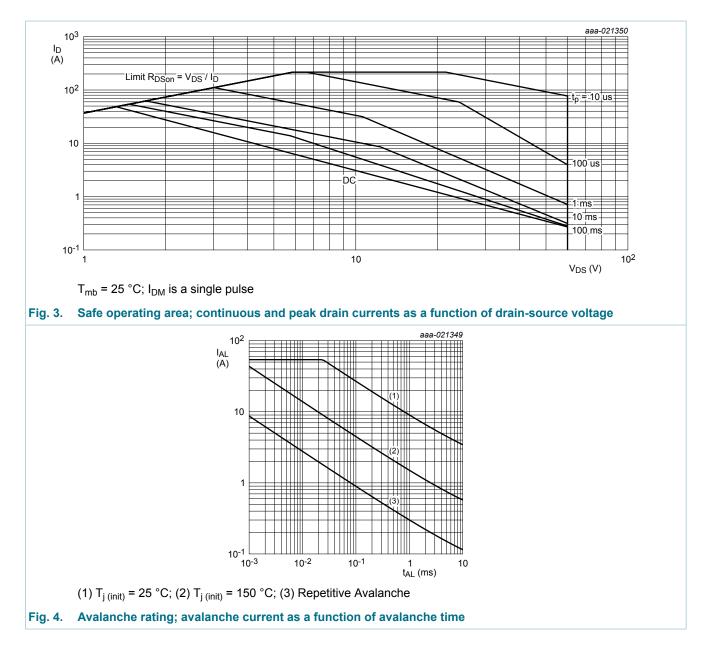
Fig. 2. Continuous drain current as a function of mounting base temperature

$$I_D = 54 \times \sqrt{\frac{175^{\circ}C - T_{mb}}{150^{\circ}C}} \text{ for } T_{mb} \ge 25^{\circ}C$$

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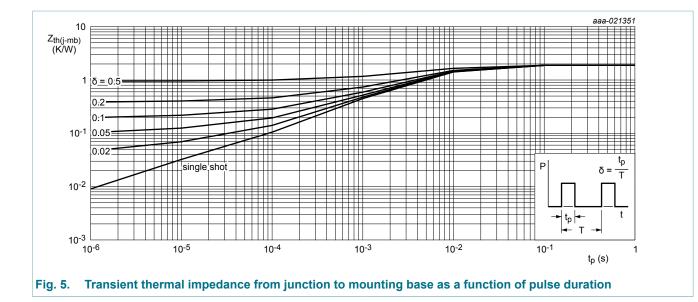


9. Thermal characteristics

Table 6. Th	ermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	1.58	1.89	K/W

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N-channel 60 V, 12 mΩ logic level MOSFET in LFPAK33



10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · ·	I			
V _{(BR)DSS} drain-source breakdown voltage		I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	60	-	-	V
	I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	54	-	-	V	
V _{GS(th)}	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; Fig. 9; Fig. 10	1.4	1.7	2.1	V
	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10	-	-	2.45	V	
	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 10	0.5	-	-	V	
I _{DSS}	DSS drain leakage current	V_{DS} = 60 V; V_{GS} = 0 V; T_j = 25 °C	-	0.02	1	μA
	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA	
I _{GSS} gate leakage current	V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA	
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 5 V; I _D = 15 A; T _j = 25 °C; <u>Fig. 11</u>	-	10	12	mΩ
	resistance	V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; <u>Fig. 11</u>	-	9	11	mΩ
		V _{GS} = 5 V; I _D = 15 A; T _j = 175 °C; Fig. 12	-	-	27	mΩ
Dynamic ch	aracteristics		1		1	
Q _{G(tot)}	total gate charge	I _D = 15 A; V _{DS} = 48 V; V _{GS} = 5 V;	-	21	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 13; Fig. 14</u>	-	5.4	-	nC

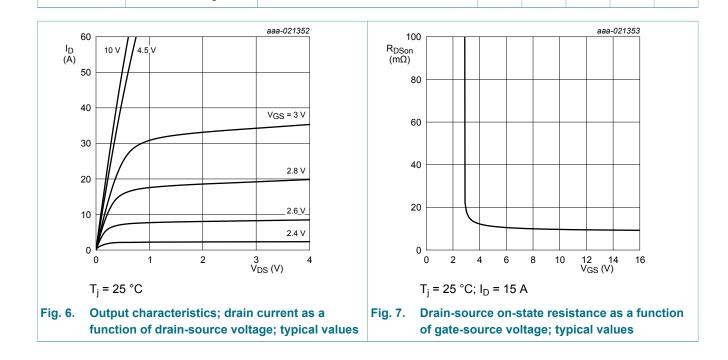
Qr

recovered charge

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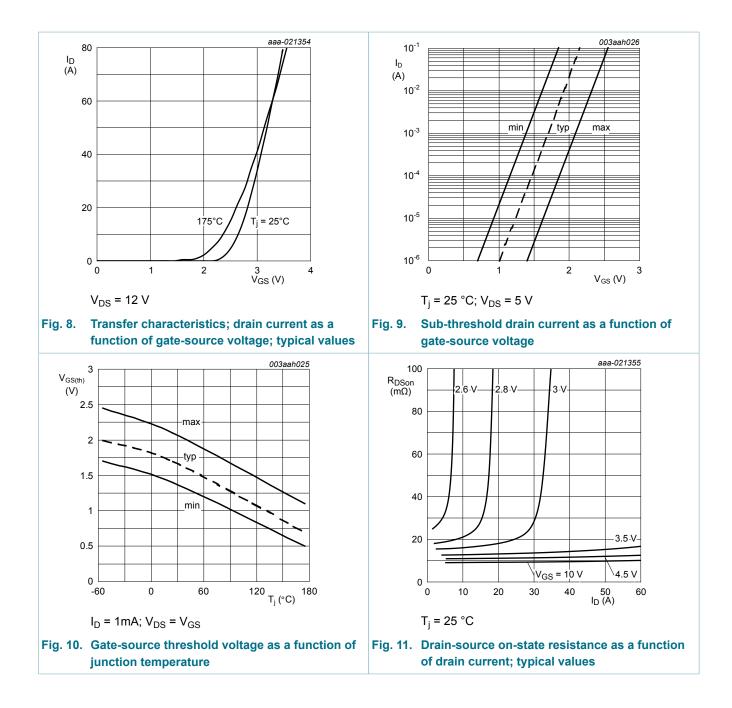
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Q _{GD}	gate-drain charge		-	7.9	-	nC
C _{iss}	input capacitance	V_{DS} = 25 V; V_{GS} = 0 V; f = 1 MHz;	-	2082	2769	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>	-	195	234	pF
C _{rss}	reverse transfer capacitance		-	101	138	pF
t _{d(on)}	turn-on delay time	V_{DS} = 45 V; R _L = 3 Ω; V _{GS} = 5 V;	-	12.1	-	ns
t _r	rise time	R _{G(ext)} = 5 Ω; T _j = 25 °C	-	21.3	-	ns
t _{d(off)}	turn-off delay time		-	26.5	-	ns
t _f	fall time	-	-	17.4	-	ns
Source-dra	in diode					
V _{SD}	source-drain voltage	I_{S} = 15 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 16</u>	-	0.82	1.2	V
t _{rr}	reverse recovery time	I _S = 15 A; dI _S /dt = -100 A/μs; V _{GS} = 0 V;	-	20.1	-	ns
Qr	recovered charge	V _{DS} = 25 V; T _j = 25 °C	_	16.5	-	nC



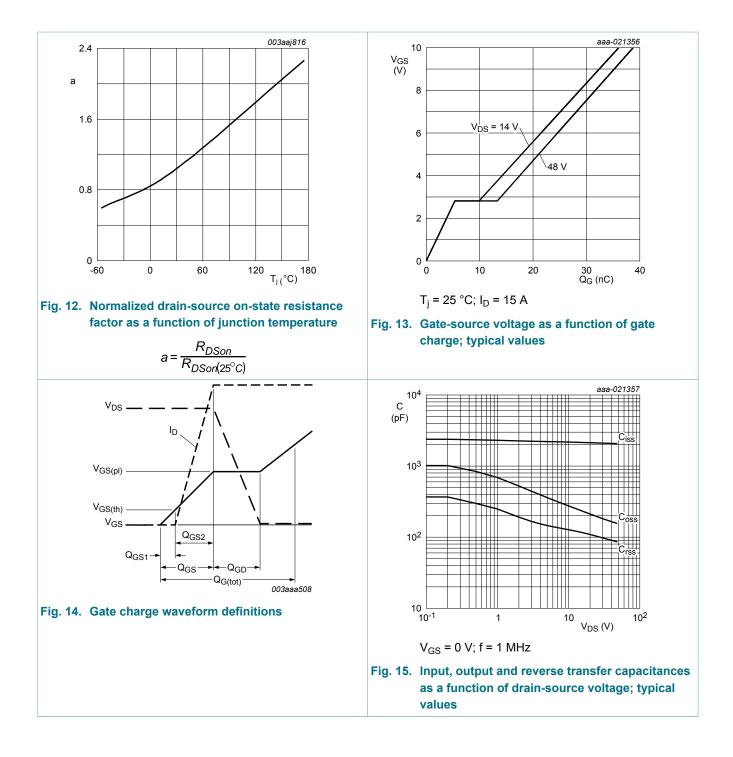
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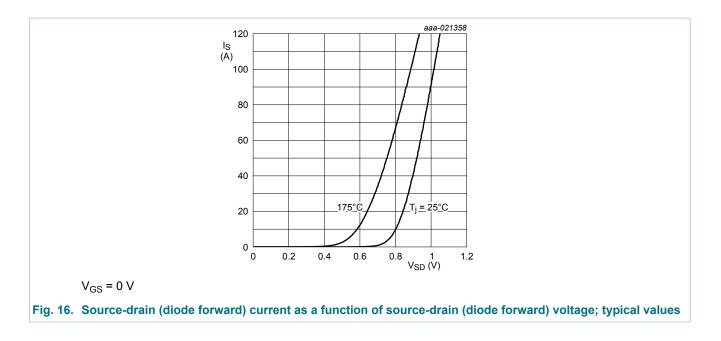
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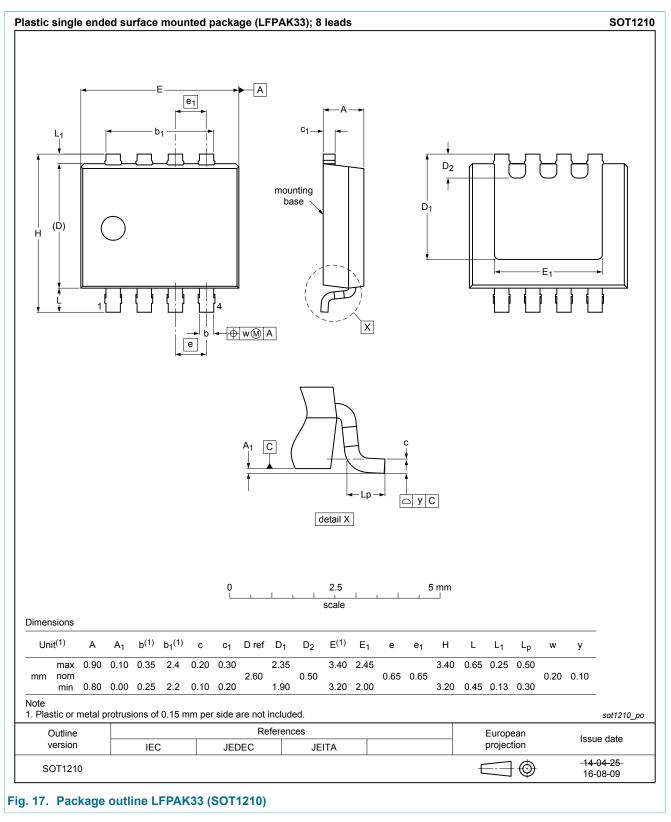
11. Application information

For guidance on how to use and understand this datasheet, please refer to application note <u>AN11158</u> "Understanding power MOSFET datasheet parameters".

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12. Package outline



BUK9M12-60E

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Product data sheet

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N-channel 60 V, 12 mΩ logic level MOSFET in LFPAK33

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Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

 Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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